MOSFET – P-Channel, QFET®

FQD3P50
-500 V, 4.9 Ω, -2.1 A

Description

This P−Channel enhancement mode power MOSFET is produced using ON Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on−state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

Features

- −2.1 A, −500 V, $R_{DS(on)}$ = 4.9 Ω (Max.) @ V_{GS} = −10 V, I_D = −1.05 A
- Low Gate Charge (Typ. 18 nC)
- Low Crss (Typ. 9.5 pF)
- 100% Avalanche Tested
- These Devices are Pb−Free and are RoHS Compliant

ABSOLUTE MAXIMUM RATINGS (T_C = 20°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{DSS}	Drain−Source Voltage	−500	V
I_D	Drain Current − Continuous (T_C = 25°C) − Continuous (T_C = 100°C)	 −2.1 −1.33	A
I_{DM}	Drain Current − Pulsed (Note 1)	−8.4	A
V_{GSS}	Gate−Source Voltage	±30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	250	mJ
I_{AR}	Avalanche Current (Note 1)	−2.1	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	5.0	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	−4.5	V/ns
P_D	Power Dissipation (T_A = 25°C) (Note 4)	2.5	W
	Power Dissipation (T_C = 25°C) − Derate above 25°C	50 0.4	W W/°C
T_J, T_{STG}	Operating and Storage Temperature Range	−55 to +150	°C
T_L	Maximum lead temperature for soldering purposes, 1/8″ from case for 5 seconds	300	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. L = 102 mH, I_{AS} = −2.1 A, V_{DD} = −50 V, R_G = 25 Ω, Starting T_J = 25°C.
3. I_{SD} ≤ −2.7 A, di/dt ≤ 200 A/ms, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C.
4. When mounted on the minimum pad size recommended (PCB Mount).

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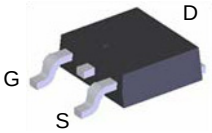

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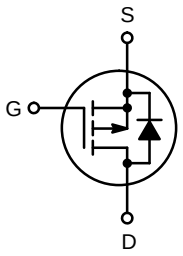
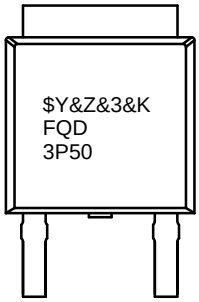


MARKING DIAGRAM



$Y	= ON Semiconductor Logo
&Z	= Assembly Code
&3	= Date Code (Year and Week)
&K	= Lot Code
FQD3P50	= Specific Device Code

ORDERING INFORMATION

Device	Package	Shipping†
FQD3P50	DPAK3 (Pb−Free)	2,500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

THERMAL CHARACTERISTICS

Symbol	Parameter	FQD3P50	Unit
$R_{\theta JC}$	Thermal Resistance, Junction−to−Case, Max.	2.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction−to−Ambient, Max. (Note 5)	50	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction−to−Ambient, Max.	110	°C/W

5. When mounted on the minimum pad size recommended (PCB Mount).

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
BV_{DSS}	Drain−Source Breakdown Voltage	V_{GS} = 0 V, I_D = −250 mA	−500	–	–	V
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temperature Coefficient	I_D = −250 mA, Referenced to 25°C	–	0.42	–	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = −500 V, V_{GS} = 0 V	–	–	−1	μA
		V_{DS} = −400 V, T_C = 125°C	–	–	−10	μA
I_{GSSF}	Gate−Body Leakage Current, Forward	V_{GS} = −30 V, V_{DS} = 0 V	–	–	−100	nA
I_{GSSR}	Gate−Body Leakage Current, Reverse	V_{GS} = 30 V, V_{DS} = 0 V	–	–	100	nA
ON CHARACTERISTICS						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = −250 mA	−3.0	–	−5.0	V
$R_{DS(on)}$	Static Drain−Source On−Resistance	V_{GS} = −10 V, I_D = −1.05 A	–	3.9	4.9	Ω
g_{FS}	Forward Transconductance	V_{DS} = −50 V, I_D = −1.05 A	–	2.1	–	S
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	V_{DS} = −25 V, V_{GS} = 0 V, f = 1.0 MHz	–	510	660	pF
C_{oss}	Output Capacitance		–	70	90	pF
C_{rss}	Reverse Transfer Capacitance		–	9.5	12	pF
SWITCHING CHARACTERISTICS						
$t_{d(on)}$	Turn−On Delay Time	V_{DD} = −250 V, I_D = −2.7 A, R_G = 25 Ω (Note 6)	–	12	35	ns
t_r	Turn−On Rise Time		–	56	120	ns
$t_{d(off)}$	Turn−Off Delay Time		–	35	80	ns
t_f	Turn−Off Fall Time		–	45	100	ns
Q_g	Total Gate Charge	V_{DS} = −400 V, I_D = −2.7 A, V_{GS} = −10 V (Note 6)	–	18	23	nC
Q_{gs}	Gate−Source Charge		–	3.6	–	nC
Q_{gd}	Gate−Drain Charge		–	9.2	–	nC
DRAIN−SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
I_S	Maximum Continuous Drain−Source Diode Forward Current		–	–	−2.1	A
I_{SM}	Maximum Pulsed Drain−Source Diode Forward Current		–	–	−8.4	A
V_{SD}	Drain−Source Diode Forward Voltage	V_{GS} = 0 V, I_S = −2.1 A	–	–	−5.0	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_S = −2.7 A, dI_F / dt = 100 A/ms	–	270	–	ns
Q_{rr}	Reverse Recovery Charge		–	1.5	–	μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

6. Essentially independent of operating temperature.

TYPICAL PERFORMANCE CURVES

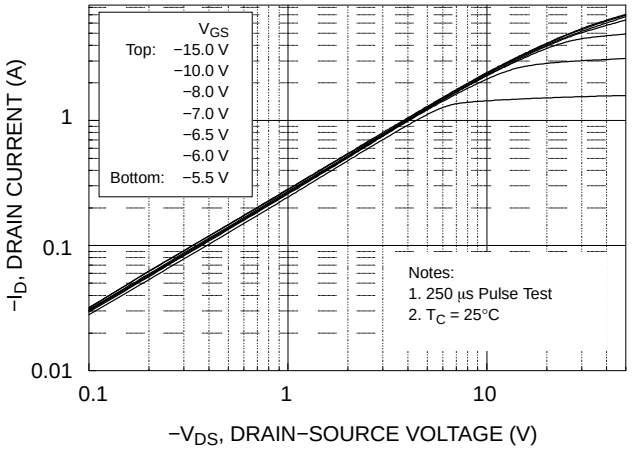


Figure 1. On−Region Characteristics

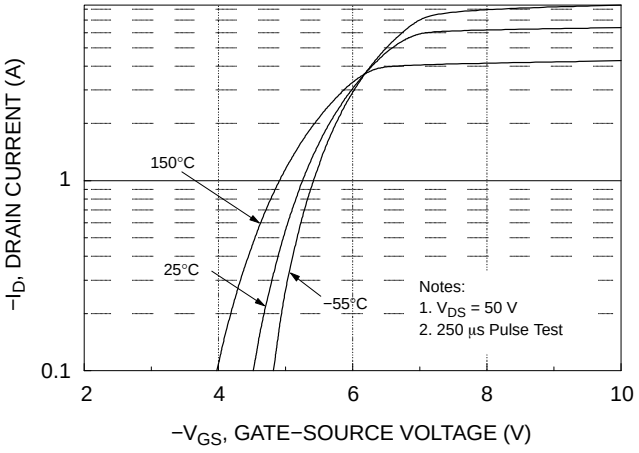


Figure 2. Transfer Characteristics

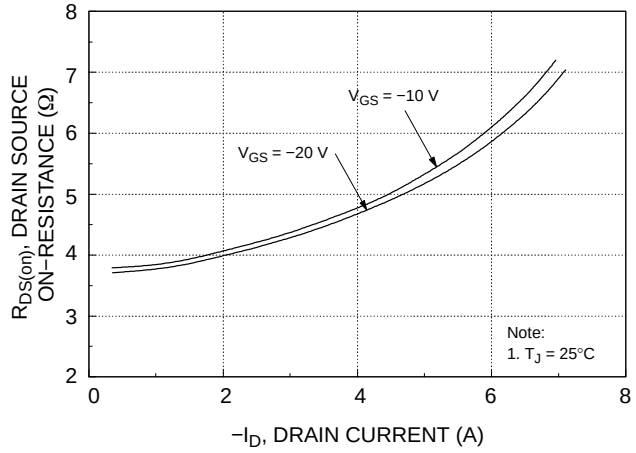


Figure 3. On−Resistance Variation vs. Drain Current and Gate Voltage

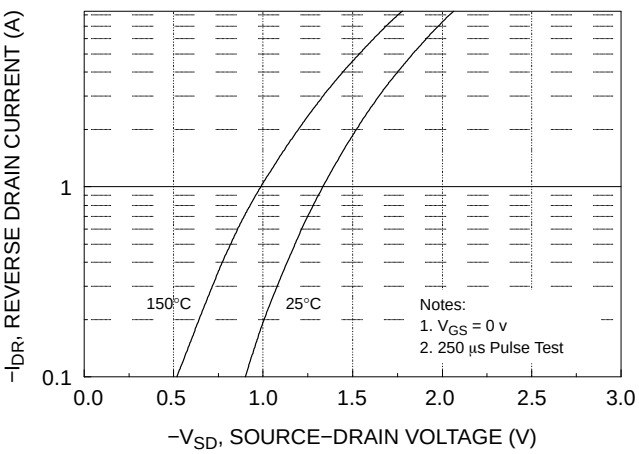


Figure 4. Body Diode Forward Voltage Variant vs. Source Current and Temperature

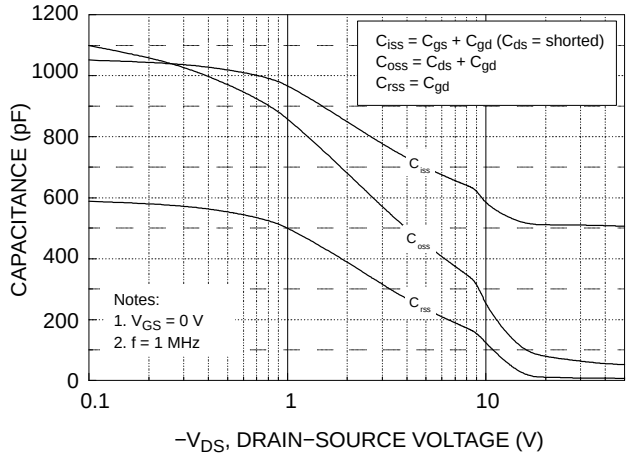


Figure 5. Capacitance Characteristics

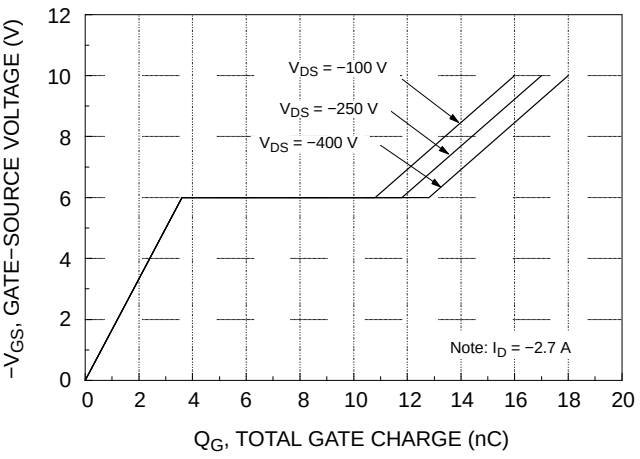


Figure 6. Gate Charge Characteristics

TYPICAL PERFORMANCE CURVES (CONTINUED)

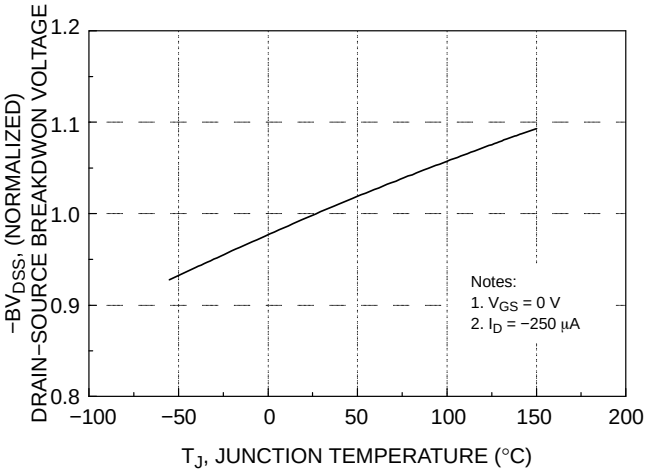


Figure 7. Breakdown Voltage Variation vs. Temperature

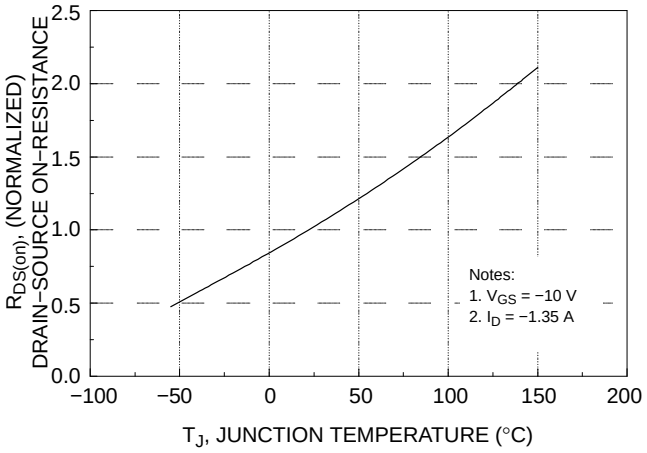


Figure 8. On−Resistance Variation vs. Temperature

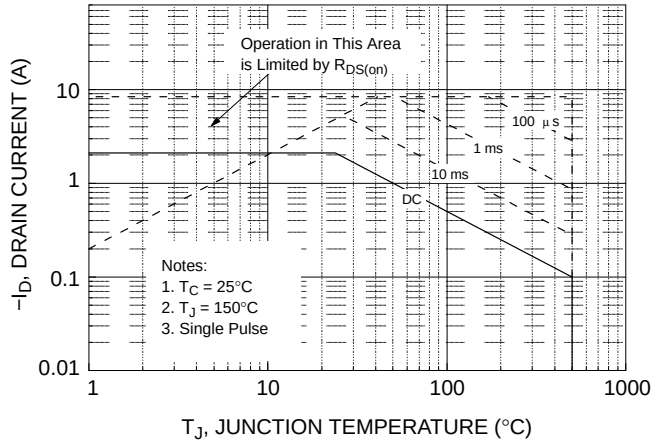


Figure 9. Maximum Safe Operation Area

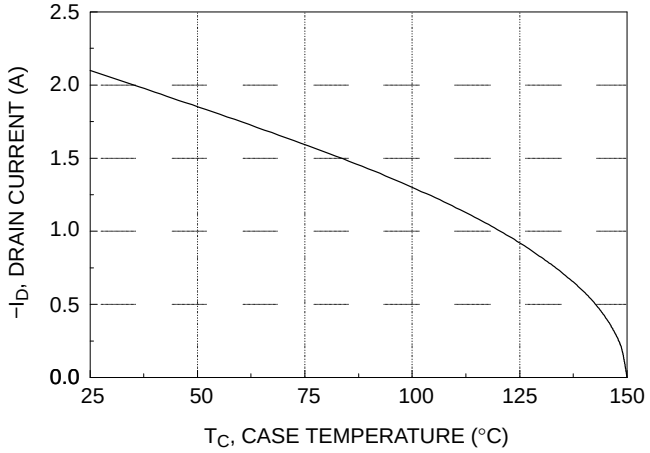


Figure 10. Maximum Drain Current vs. Case Temperature

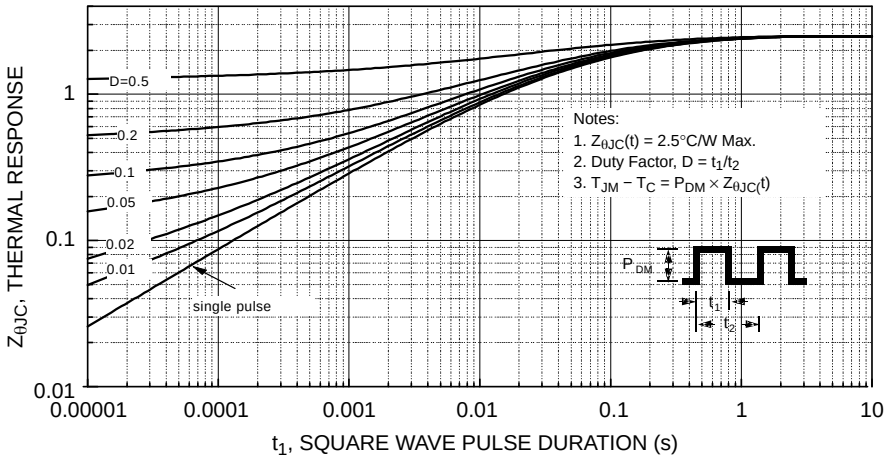


Figure 11. Transient Thermal Response Curve

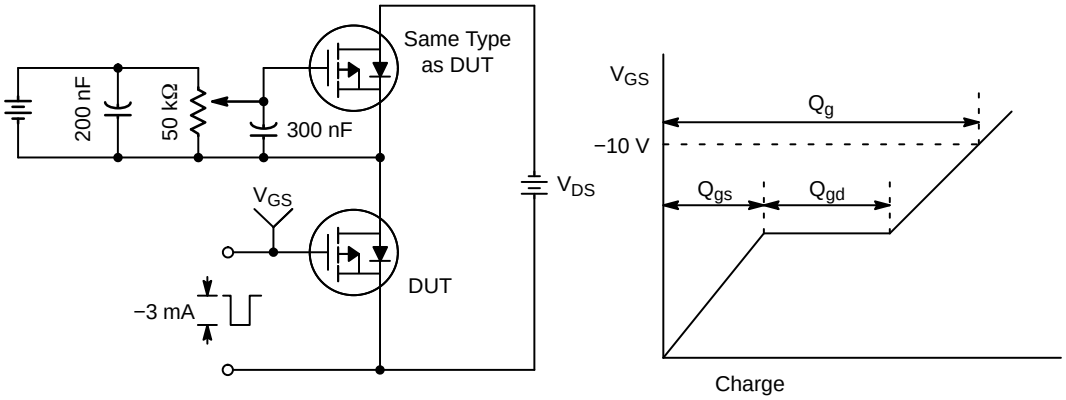


Figure 12. Gate Charge Test Circuit & Waveform

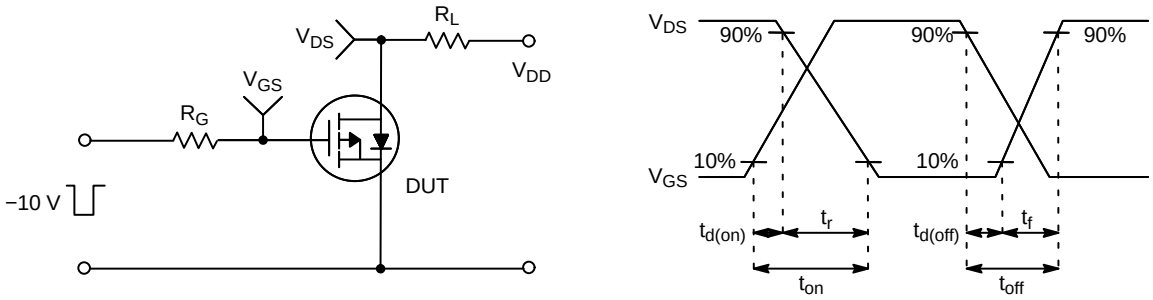


Figure 13. Resistive Switching Test Circuit & Waveforms

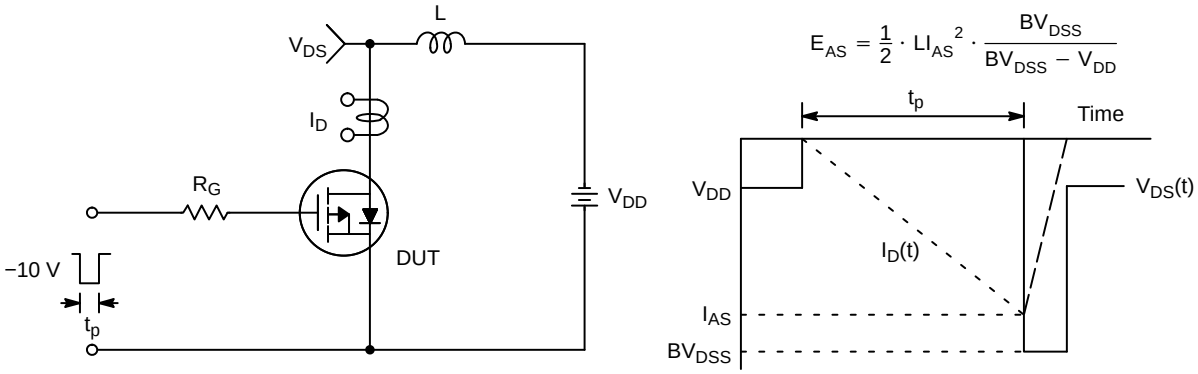


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

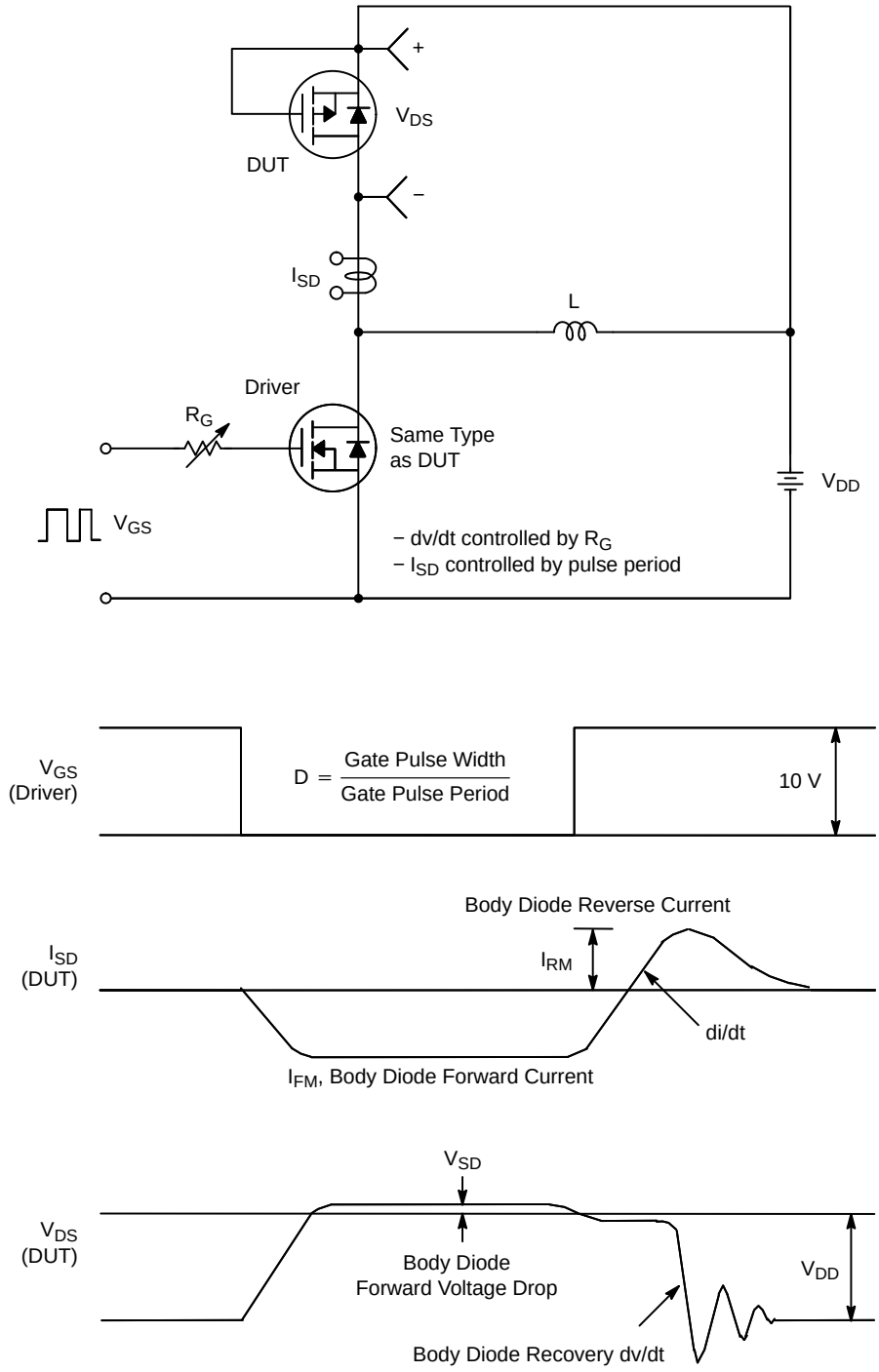


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

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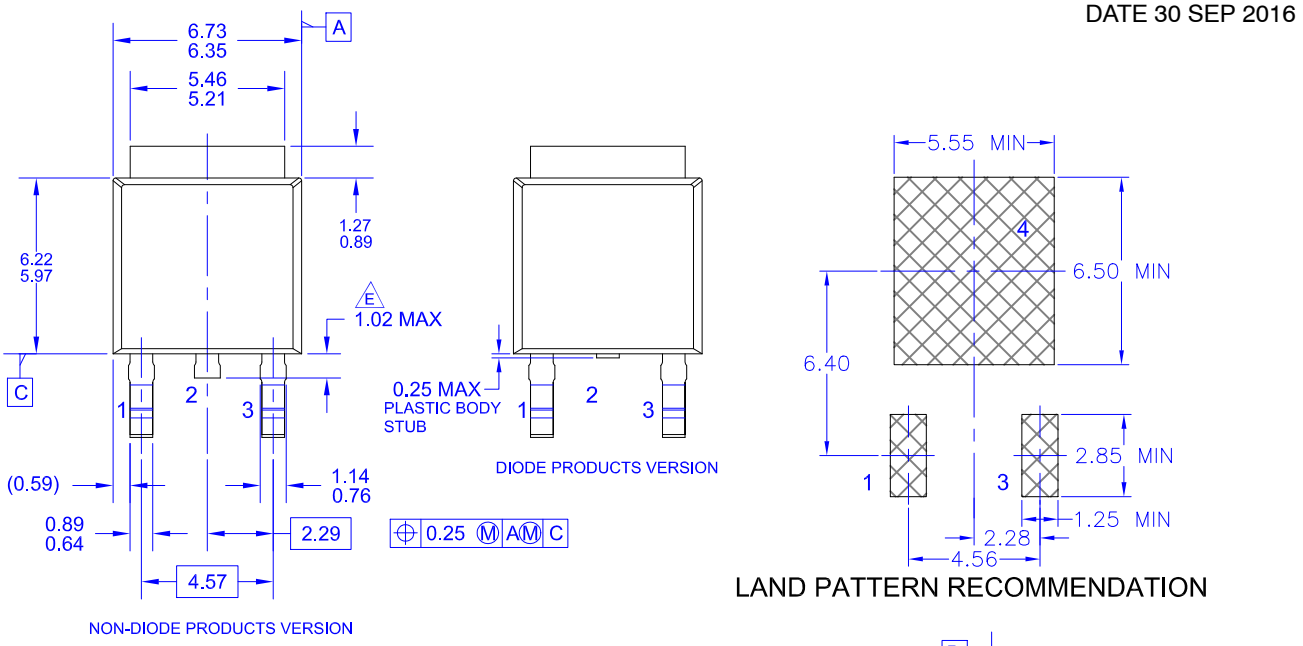

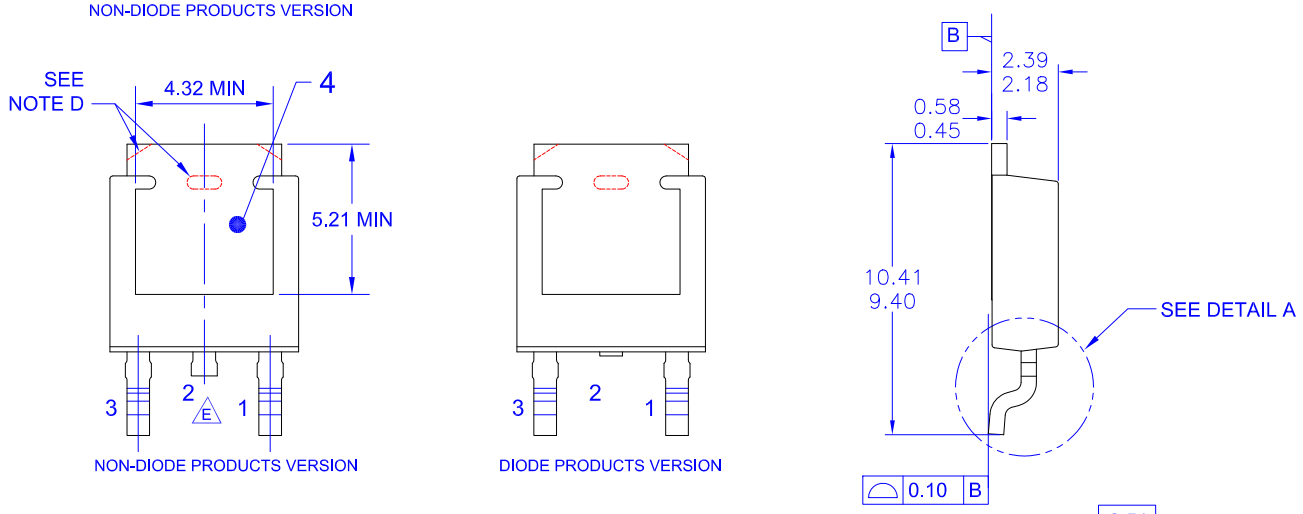

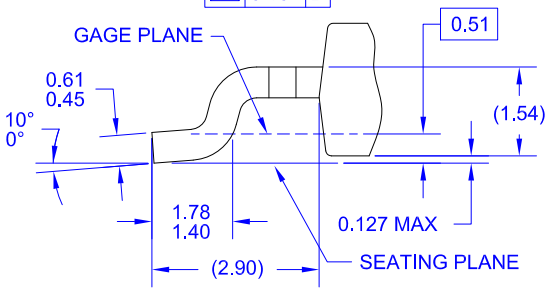

NOTES: UNLESS OTHERWISE SPECIFIED
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B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED CORNERS OR EDGE PROTRUSION.
E) TRIMMED CENTER LEAD IS PRESENT ONLY FOR DIODE PRODUCTS
F) DIMENSIONS ARE EXCLUSSIVE OF BURSS, MOLD FLASH AND TIE BAR EXTRUSIONS.
G) LAND PATTERN RECOMENDATION IS BASED ON IPC7351A STD TO228P991X239-3N.

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